

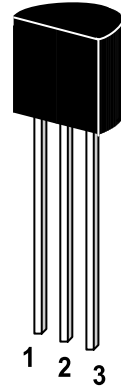
ST 2SC3279

NPN Silicon Epitaxial Planar Transistor

for storobo flash and medium power amplifier applications.

The transistor is subdivided into four groups L, M, N and P, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



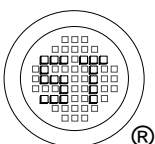
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25°C)

		Symbol	Value	Unit
Collector Base Voltage		V_{CBO}	30	V
Collector Emitter Voltage		V_{CES}	30	V
		V_{CEO}	10	
Emitter Base Voltage		V_{EBO}	6	V
Collector Current	Pulsed(Note 1)	I_{CP}	5	A
	DC	I_C	2	A
Base Current		I_B	0.2	A
Power Dissipation		P_{tot}	750	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_S	-55 to +150	°C

Note 1: Pulse Width=10ms (Max.), Duty Cycle=30%(Max.)



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ISO/TS 16949 : 2002
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ISO 14001:2004
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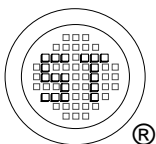
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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=1\text{V}$, $I_C=0.5\text{A}$	L	h_{FE}	140	-	240	-
	M	h_{FE}	200	-	330	-
	N	h_{FE}	300	-	450	-
	P	h_{FE}	420	-	600	-
	at $V_{CE}=1\text{V}$, $I_C=2\text{A}$	h_{FE}	70	200	-	-
Collector Cutoff Current at $V_{CB}=30\text{V}$	I_{CBO}	-	-	0.1	μA	
Emitter Cutoff Current at $V_{EB}=6\text{V}$	I_{EBO}	-	-	0.1	μA	
Collector-Emitter Breakdown Voltage at $I_C=10\text{mA}$	$V_{(BR)CEO}$	10	-	-	V	
Emitter-Base Breakdown Voltage at $I_E=1\text{mA}$	$V_{(BR)EBO}$	6	-	-	V	
Collector Output Capacitance at $V_{CB}=10\text{V}$, $f=1.0\text{MHz}$	C_{ob}	-	27	-	pF	
Collector to Emitter Saturation Voltage at $I_C=2\text{A}$, $I_B=50\text{mA}$	$V_{CE(sat)}$	-	0.2	0.5	V	
Base-Emitter Voltage at $V_{CE}=1\text{V}$, $I_C=2\text{A}$	V_{BE}	-	0.86	1.5	V	
Transition Frequency at $V_{CE}=1\text{V}$, $I_C=0.5\text{A}$	f_T	-	150	-	MHz	



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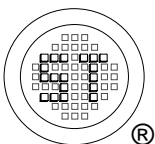
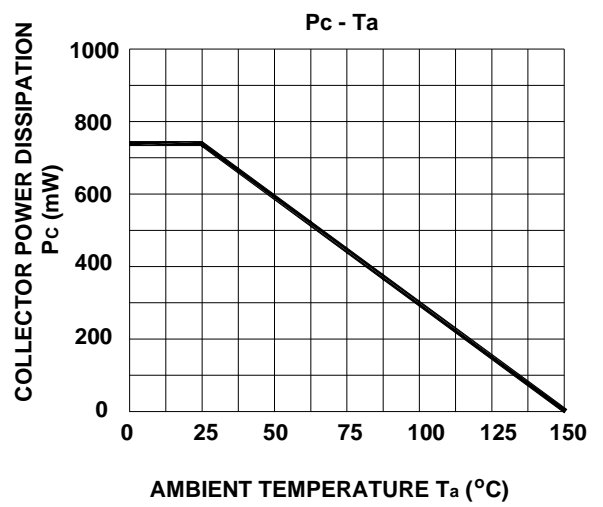
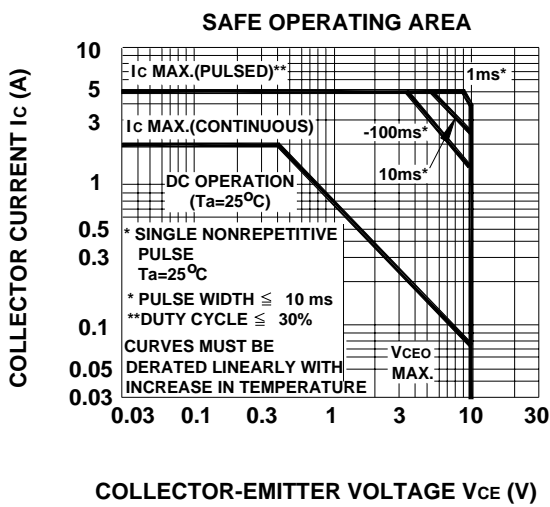
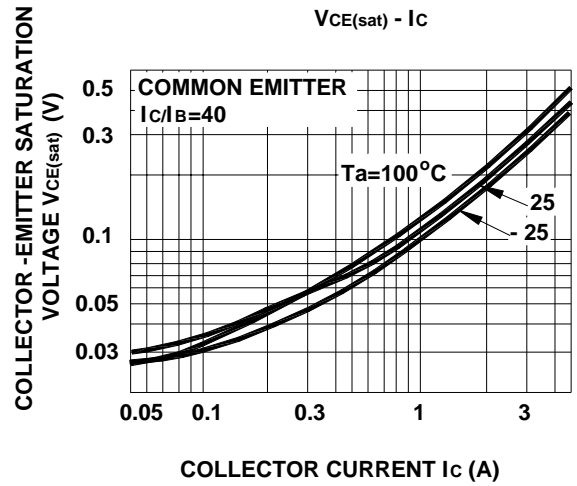
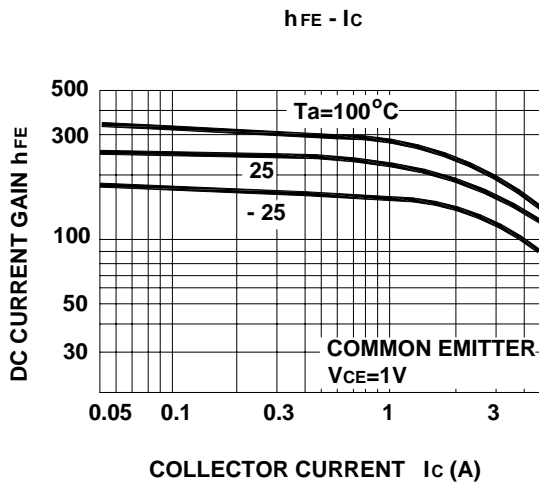
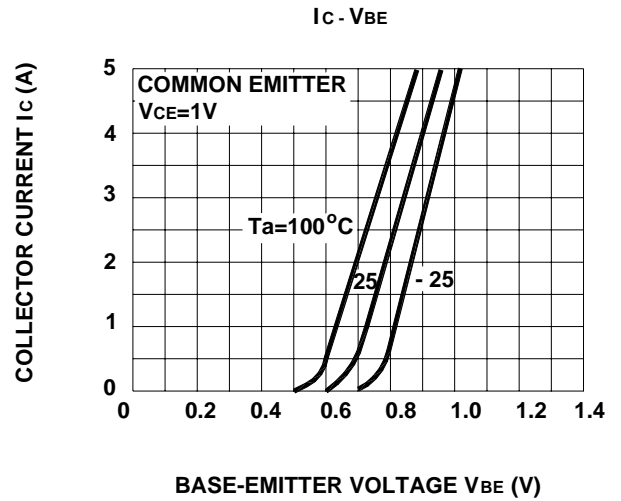
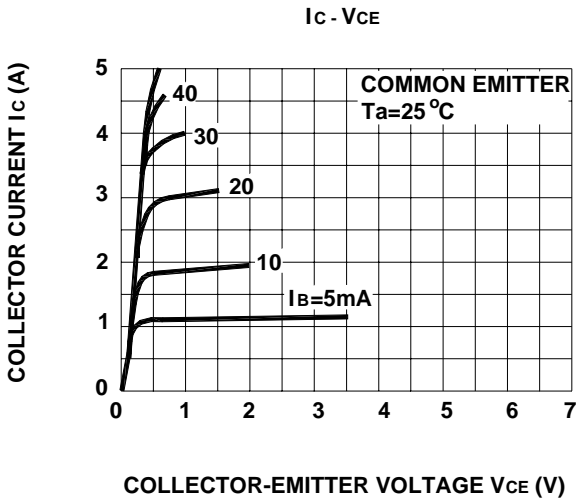
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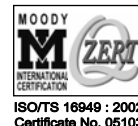
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